

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. 2271/62289-Z		Serial No. 10/601, Not Yet Assigned 301	
INFORMATION DISCLOSURE CITATION BY APPLICANT (Use several sheets if necessary)				Applicant Seiji SARAYAMA et al.			
				Filing Date		Group 2818	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
TH	AA	6 2 7 0 5 6 9	08/2001	Shibata et al.			
TH	AB	6 1 7 7 0 5 7	01/2001	Purdy			
TH	AC	5 8 6 8 8 3 7	02/1999	DiSalvo et al.			
	AD						
	AE						
	AF						
	AG						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AH						
	AI						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
TH	AJ	"Preparation of GaN Single Crystals Using a Na Flux", H. Yamane et al., Chemical Mater, 1997, Vol. 9, No. 2, pp. 413-416.					
TH	AK	"InGaN/GaN/AlGaIn-Based Laser Diodes With Cleaved Facets Grown on GaN Substrates", S. Nakamura et al., Applied Physics Letters, 1998, Vol. 73, No. 6, pp. 832-834.					
TH	AL	"Bulk and Homoepitaxial GaN-growth and Characterization", S. Porowski, Journal of Crystal Growth, 1998, Vol. 189/190, pp.153-158.					
TH	AM	"InGaN/GaN/AlGaIn-Based Laser Diodes With Modulation-Doped Strained-Layer Superlattices", S. Nakamura et al., Japanese Journal of Applied Physics, 1997, Vol. 36, No. 12A, pp. 1568-1571.					
	AN						
EXAMINER		TU TE HO		DATE CONSIDERED Feb, 2005			
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